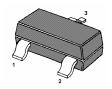
BC817 / BC818

NPN Silicon Epitaxial Planar Transistors

for switching, AF driver and amplifier application,

These transistors are subdivided into three groups -16, -25, -40 according to their current gain. As complementary types, the PNP transistors BC807 and BC808 are recommended.



1. Base 2. Emitter 3. Collector SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit	
Collector Base Voltage	BC817 BC818	V _{CBO}	50 30	V	
Collector Emitter Voltage	BC817 BC818	V _{CEO}	45 25	V	
Emitter Base Voltage		V_{EBO}	5	V	
Collector Current		Ic	500	mA	
Power Dissipation		P _{tot}	200	mW	
Thermal Resistance , Junction to Ambient		$R_{ heta JA}$	500	K/W	
Junction Temperature		TJ	150	°C	
Storage Temperature Range		T _s	- 55 to + 150	°C	

Electrical Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at $V_{CE} = 1 \text{ V}$, $I_C = 100 \text{ mA}$ Current Gain Gro	up -16	h _{FE}	100	-	250	-
	-25	h_FE	160	-	400	-
	-40	h_FE	250	-	600	-
at $V_{CE} = 1 \text{ V}, I_C = 500 \text{ mA}$		h _{FE}	40	-	-	-
Collector Base Cutoff Current at V _{CB} = 20 V		I _{CBO}	-	-	100	nA
Emitter-Base Cutoff Current at V _{EB} = 5 V		I _{EBO}	-	-	100	nA
Collector Saturation Voltage at $I_C = 500$ mA, $I_B = 50$ mA		V _{CEsat}	-	-	0.7	V
Base-Emitter Voltage at $I_C = 500 \text{ mA}$, $V_{CE} = 1 \text{ V}$		V _{BE(on)}	-	-	1.2	V
Gain -Bandwidth Product at $V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 50 \text{ MHz}$		f _T	100	-	-	MHz
Collector-Base Capacitance at $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$		C _{CBO}	-	5	-	pF



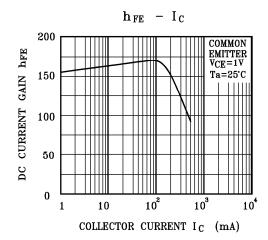


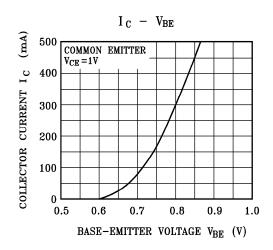


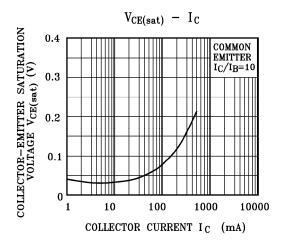


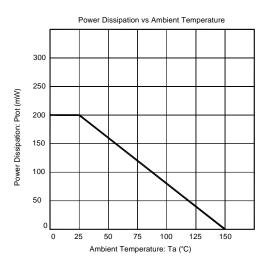


Dated: 19/12/2005











SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







Dated: 19/12/2005